

LF412

Low Offset, Low Drift Dual JFET Input Operational Amplifier

General Description

These devices are low cost, high speed, JFET input operational amplifiers with very low input offset voltage and guaranteed input offset voltage drift. They require low supply current yet maintain a large gain bandwidth product and fast slew rate. In addition, well matched high voltage JFET input devices provide very low input bias and offset currents. The LF412 dual is pin compatible with the LM1558, allowing designers to immediately upgrade the overall performance of existing designs.

These amplifiers may be used in applications such as high speed integrators, fast D/A converters, sample and hold circuits and many other circuits requiring low input offset voltage and drift, low input bias current, high input impedance, high slew rate and wide bandwidth.

Features

■ Internally trimmed offset voltage: 1 mV (max)

■ Input offset voltage drift: 10 µV/°C (max)

■ Low input bias current: 50 pA

■ Low input noise current: 0.01 pA/√Hz

■ Wide gain bandwidth: 3 MHz (min)

■ High slew rate: 10V/µs (min)

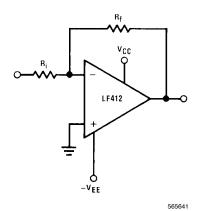
■ Low supply current: 1.8 mA/Amplifier

■ High input impedance: 10¹²Ω

■ Low total harmonic distortion ≤0.02%

■ Low 1/f noise corner: 50 Hz ■ Fast settling time to 0.01%: 2 µs

Typical Connection



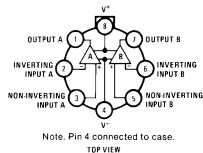
Ordering Information

LF412XYZ

- X indicates electrical grade
- Y indicates temperature range "M" for military
- "C" for commercial
- Z indicates package type "H" or "N"

Connection Diagrams

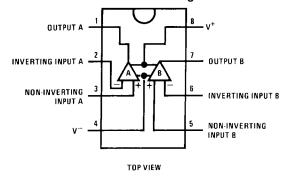
Metal Can Package



565642

Order Number LF412MH, LF412CH See NS Package Number H08A or LF412MH/883 (*Note 1*) See NS Package Number H08C

Dual-In-Line Package

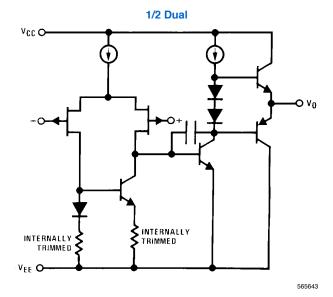


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Order Number LF412ACN, LF412CN or LF412MJ/883 (*Note 1*)
See NS Package Number J08A or N08E

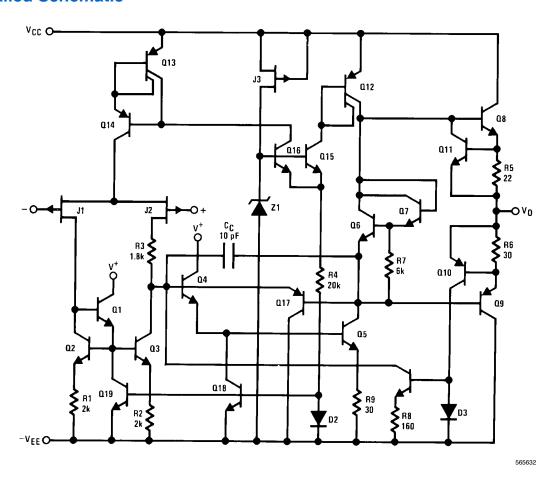
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Simplified Schematic



Note 1: Available per JM38510/11905

Detailed Schematic



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Absolute Maximum Ratings (Note 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

(Note 11)

	LF412A	LF412
Supply Voltage	±22V	±18V
Differential Input Voltage	±38V	±30V
Input voltage Range		
(Note 3)	±19V	±15V
Output Short Circuit		
Duration (Note 4)	Continuous	Continuous

	H Package	N Package
Power Dissipation		
(Note 12)	(<i>Note 5</i>)	670 mW
T _j max	150°C	115°C
θ _{iA} (Typical)	152°C/W	115°C/W
Operating Temp. Range	e (<i>Note 6</i>)	(<i>Note 6</i>)
Storage Temp.	–65°C≤T _A ≤150°	-65°C≤T _A ≤150°
	С	С
Range		
Lead Temp.		
(Soldering, 10 sec.)	260°C	260°C
ESD Tolerance		

1700V

1700V

DC Electrical Characteristics

(Note 7)

Symbol	Parameter	Conditions		LF412A			LF412			Units
				Min	Тур	Max	Min	Тур	Max	
V _{OS}	Input Offset Voltage	R _S =10 kΩ, T _A =25°C			0.5	1.0		1.0	3.0	mV
$\Delta V_{OS}/\Delta T$	Average TC of Input	R _S =10 kΩ (<i>Note 8</i>)			7	10		7	20	μV/°C
	Offset Voltage									
I _{os}	Input Offset Current	V _S =±15V	T _j =25°C		25	100		25	100	pА
		(Note 7, Note 9)	T _j =70°C			2			2	nA
			T _j =125°C			25			25	nA
I _B	Input Bias Current	V _S =±15V	T _j =25°C		50	200		50	200	pА
		(Note 7, Note 9)	T _j =70°C			4			4	nA
			T _j =125°C			50			50	nA
R _{IN}	Input Resistance	T _j =25°C			10 ¹²			10 ¹²		Ω
A _{VOL}	Large Signal Voltage	V _S =±15V, V _O =±10V,		50	200		25	200		V/mV
	Gain	R _L =2k, T _A =25°C								
		Over Temperature		25	200		15	200		V/mV
Vo	Output Voltage Swing	V _S =±15V, R _L =10k		±12	±13.5		±12	±13.5		V
V _{CM}	Input Common-Mode			±16	+19.5		±11	+14.5		V
	Voltage Range				-16.5			-11.5		V
CMRR	Common-Mode	R _S ≤10k		80	100		70	100		dB
	Rejection Ratio									
PSRR	Supply Voltage	(Note 10)	·	80	100		70	100		dB
	Rejection Ratio									
Is	Supply Current	$V_O = 0V, R_L = \infty$			3.6	5.6		3.6	6.5	mA

(Note 13)

Note 2: "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits.

AC Electrical Characteristics

(Note 7)

Symbol	Parameter	Conditions	LF412A			LF412			Units
			Min	Тур	Max	Min	Тур	Max	
	Amplifier to Amplifier	T _A =25°C, f=1 Hz-20 kHz		-120			-120		dB
	Coupling	(Input Referred)							
SR	Slew Rate	V _S =±15V, T _A =25°C	10	15		8	15		V/µs
GBW	Gain-Bandwidth Product	V _S =±15V, T _A =25°C	3	4		2.7	4		MHz